

CLAIMS

1. Method of minimizing the "corner" effect in shallow trenches (26) of silicon oxide for laterally insulating active areas (21), characterized in that after
5 depositing a layer (23) of silicon oxide into the trenches (26), said deposited layer is densified by irradiation with short wavelength light.

2. Method according to claim 1, characterized in that the oxide layer is densified by irradiating said
10 layer with light at a wavelength less than or equal to 200 nm with a number of photons per cm^2 greater than 10^{19} and an energy at least equal to 9 eV.

3. Method according to claim 2, characterized in that the wavelength of the light is approximately 100 nm.

15 ^{sub A1} 4. Method according to any of claims 1 to 3, characterized in that the layer (23) of silicon oxide deposited in the trenches (26) is densified directly after depositing said layer, before flattening it.